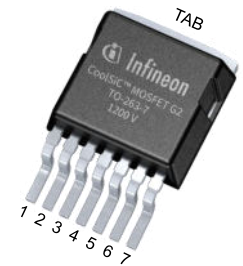


Final datasheet

CoolSiC™ 1200 V SiC MOSFET G2 : Silicon Carbide MOSFET

Features

- $V_{DSS} = 1200\text{ V}$ at $T_{vj} = 25^\circ\text{C}$
- $I_{DC} = 21\text{ A}$ at $T_C = 100^\circ\text{C}$
- $R_{DS(on)} = 78.1\text{ m}\Omega$ at $V_{GS} = 18\text{ V}$, $T_{vj} = 25^\circ\text{C}$
- Very low switching losses
- Overload operation up to $T_{vj} = 200^\circ\text{C}$
- Short circuit withstand time $2\text{ }\mu\text{s}$
- Benchmark gate threshold voltage, $V_{GS(th)} = 4.2\text{ V}$
- Robust against parasitic turn on, 0 V turn-off gate voltage can be applied
- Robust body diode for hard commutation
- .XT interconnection technology for best-in-class thermal performance
- Suitable Infineon gate drivers can be found under <https://www.infineon.com/gdfinder>



- Halogen-free
- Green
- Lead-free
- RoHS

Potential applications

- EV Charging
- Online UPS/Industrial UPS
- String inverter
- General purpose drives (GPD)

Product validation

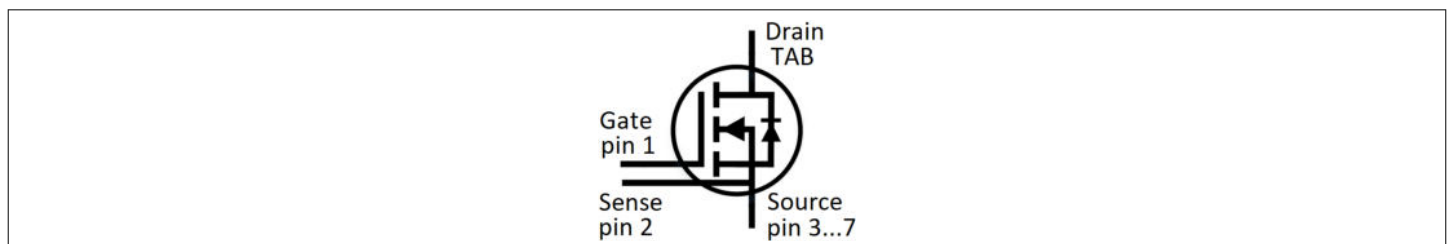
- Qualified for industrial applications according to the relevant tests of JEDEC47/20/22

Description

Pin definition:

- Pin 1 - Gate
- Pin 2 - Kelvin sense contact
- Pin 3...7 - Source
- Tab - Drain

Note: the source and sense pins are not exchangeable, their exchange might lead to malfunction (only for 4pin, TO263-7L)



Type	Package	Marking
IMBG120R078M2H	PG-TO263-7-U01	12M2H078

Table of contents

	Description	1
	Features	1
	Potential applications	1
	Product validation	1
	Table of contents	2
1	Package	3
2	MOSFET	3
3	Body diode (MOSFET)	6
4	Characteristics diagrams	8
5	Package outlines	14
6	Testing conditions	15
	Revision history	16
	Disclaimer	17

1 Package

1 Package

Table 1 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Storage temperature	T_{stg}		-55		150	°C
Soldering temperature	T_{sold}	reflow soldering (MSL1 according to JEDEC J-STD-020)			260	°C
Thermal resistance, junction-ambient	$R_{th(j-a)}$				62	K/W
MOSFET/body diode thermal resistance, junction-case	$R_{th(j-c)}$			0.73	0.95	K/W

2 MOSFET

Table 2 Maximum rated values

Parameter	Symbol	Note or test condition	Values	Unit	
Drain-source voltage	V_{DSS}	$T_{vj} \geq 25 \text{ °C}$	1200	V	
Continuous DC drain current for $R_{th(j-c,max)}$, limited by $T_{vj(max)}$	I_{DDC}	$V_{GS} = 18 \text{ V}$	$T_c = 25 \text{ °C}$	29	A
			$T_c = 100 \text{ °C}$	21	
Peak drain current, t_p limited by $T_{vj(max)}$ ¹⁾	I_{DM}	$V_{GS} = 18 \text{ V}$	63	A	
Gate-source voltage, max. transient voltage	V_{GS}	$t_p \leq 0.5 \text{ }\mu\text{s}$, $D < 0.01$	-10...25	V	
Gate-source voltage, max. static voltage ²⁾	V_{GS}		-7...23	V	
Avalanche energy, single pulse	E_{AS}	$I_D = 8.9 \text{ A}$, $V_{DD} = 50 \text{ V}$, $L = 2.8 \text{ mH}$	112	mJ	
Avalanche energy, repetitive	E_{AR}	$I_D = 8.9 \text{ A}$, $V_{DD} = 50 \text{ V}$, $L = 14.1 \text{ }\mu\text{H}$	0.56	mJ	
Short-circuit withstand time	t_{SC}	$V_{DD} \leq 800 \text{ V}$, $V_{DS,peak} < 1200 \text{ V}$, $V_{GS(on)} = 15 \text{ V}$, $T_{vj(start)} = 25 \text{ °C}$	2	μs	
Power dissipation, limited by $T_{vj(max)}$	P_{tot}		$T_c = 25 \text{ °C}$	158	W
			$T_c = 100 \text{ °C}$	79	

1) verified by design.

2) The maximum gate-source voltage in the application design should be in accordance to IPC-9592B.

Table 3 Recommended values

Parameter	Symbol	Note or test condition	Values	Unit
Recommended turn-on gate voltage	$V_{GS(on)}$		15...18	V
Recommended turn-off gate voltage	$V_{GS(off)}$		-5...0	V

Table 4 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Drain-source on-state resistance	$R_{DS(on)}$	$I_D = 8.9\text{ A}$	$T_{vj} = 25\text{ °C}$, $V_{GS(on)} = 18\text{ V}$	78.1		mΩ
			$T_{vj} = 150\text{ °C}$, $V_{GS(on)} = 18\text{ V}$	159	206	
			$T_{vj} = 175\text{ °C}$, $V_{GS(on)} = 18\text{ V}$	185		
			$T_{vj} = 25\text{ °C}$, $V_{GS(on)} = 15\text{ V}$	97.5		
Gate-source threshold voltage	$V_{GS(th)}$	$I_D = 2.8\text{ mA}$, $V_{DS} = V_{GS}$ (tested after 1 ms pulse at $V_{GS} = 20\text{ V}$)	$T_{vj} = 25\text{ °C}$	3.5	4.2	V
			$T_{vj} = 175\text{ °C}$		3.2	
Zero gate-voltage drain current	I_{DSS}	$V_{DS} = 1200\text{ V}$, $V_{GS} = 0\text{ V}$	$T_{vj} = 25\text{ °C}$		80	μA
			$T_{vj} = 175\text{ °C}$		1.3	
Gate leakage current	I_{GSS}	$V_{DS} = 0\text{ V}$	$V_{GS} = 23\text{ V}$		120	nA
			$V_{GS} = -10\text{ V}$		-120	
Forward transconductance	g_{fs}	$I_D = 8.9\text{ A}$, $V_{DS} = 20\text{ V}$		6		S
Internal gate resistance	$R_{G,int}$	$f = 1\text{ MHz}$, $V_{AC} = 25\text{ mV}$		10		Ω
Input capacitance	C_{iss}	$V_{DS} = 800\text{ V}$, $V_{GS} = 0\text{ V}$, $f = 100\text{ kHz}$, $V_{AC} = 25\text{ mV}$		700		pF
Output capacitance	C_{oss}	$V_{DS} = 800\text{ V}$, $V_{GS} = 0\text{ V}$, $f = 100\text{ kHz}$, $V_{AC} = 25\text{ mV}$		28		pF
Reverse transfer capacitance	C_{rss}	$V_{DS} = 800\text{ V}$, $V_{GS} = 0\text{ V}$, $f = 100\text{ kHz}$, $V_{AC} = 25\text{ mV}$		2.4		pF
C_{oss} stored energy	E_{oss}	$V_{DS} = 0...800\text{ V}$, $V_{GS} = 0\text{ V}$, $f = 100\text{ kHz}$, $V_{AC} = 25\text{ mV}$, Calculated based on C_{oss}		12		μJ
Output charge	Q_{oss}	$V_{DS} = 0...800\text{ V}$, $V_{GS} = 0\text{ V}$, Calculated based on C_{oss}		43.4		nC
Effective output capacitance, energy related	$C_{o(er)}$	$V_{DS} = 0...800\text{ V}$, $V_{GS} = 0\text{ V}$		37.5		pF
Effective output capacitance, time related	$C_{o(tr)}$	$I_D = \text{constant}$, $V_{DS} = 0...800\text{ V}$, $V_{GS} = 0\text{ V}$		54.2		pF

(table continues...)

Table 4 (continued) Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Total gate charge	Q_G	$V_{DD} = 800\text{ V}$, $I_D = 8.9\text{ A}$, $V_{GS} = -2/18\text{ V}$, turn-on pulse		20.6		nC
Plateau gate charge	$Q_{GS(pl)}$	$V_{DD} = 800\text{ V}$, $I_D = 8.9\text{ A}$, $V_{GS} = -2/18\text{ V}$, turn-on pulse		4.6		nC
Gate-to-drain charge	Q_{GD}	$V_{DD} = 800\text{ V}$, $I_D = 8.9\text{ A}$, $V_{GS} = -2/18\text{ V}$, turn-on pulse		5.3		nC
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 800\text{ V}$, $I_D = 8.9\text{ A}$, $V_{GS} = 0/18\text{ V}$, $R_{GS(on)} = 2.3\ \Omega$, $R_{GS(off)} = 2.3\ \Omega$, $L_\sigma = 15\text{ nH}$, diode: body diode at $V_{GS} = 0\text{ V}$	$T_{vj} = 25\text{ }^\circ\text{C}$	2		ns
			$T_{vj} = 175\text{ }^\circ\text{C}$		1.7	
Rise time	t_r	$V_{DD} = 800\text{ V}$, $I_D = 8.9\text{ A}$, $V_{GS} = 0/18\text{ V}$, $R_{GS(on)} = 2.3\ \Omega$, $R_{GS(off)} = 2.3\ \Omega$, $L_\sigma = 15\text{ nH}$, diode: body diode at $V_{GS} = 0\text{ V}$	$T_{vj} = 25\text{ }^\circ\text{C}$		13.4	ns
			$T_{vj} = 175\text{ }^\circ\text{C}$		13.3	
Turn-off delay time	$t_{d(off)}$	$V_{DD} = 800\text{ V}$, $I_D = 8.9\text{ A}$, $V_{GS} = 0/18\text{ V}$, $R_{GS(on)} = 2.3\ \Omega$, $R_{GS(off)} = 2.3\ \Omega$, $L_\sigma = 15\text{ nH}$, diode: body diode at $V_{GS} = 0\text{ V}$	$T_{vj} = 25\text{ }^\circ\text{C}$		3.4	ns
			$T_{vj} = 175\text{ }^\circ\text{C}$		6	
Fall time	t_f	$V_{DD} = 800\text{ V}$, $I_D = 8.9\text{ A}$, $V_{GS} = 0/18\text{ V}$, $R_{GS(on)} = 2.3\ \Omega$, $R_{GS(off)} = 2.3\ \Omega$, $L_\sigma = 15\text{ nH}$, diode: body diode at $V_{GS} = 0\text{ V}$	$T_{vj} = 25\text{ }^\circ\text{C}$		2	ns
			$T_{vj} = 175\text{ }^\circ\text{C}$		2.4	
Turn-on energy	E_{on}	$V_{DD} = 800\text{ V}$, $I_D = 8.9\text{ A}$, $V_{GS} = 0/18\text{ V}$, $R_{GS(on)} = 2.3\ \Omega$, $R_{GS(off)} = 2.3\ \Omega$, $L_\sigma = 15\text{ nH}$, diode: body diode at $V_{GS} = 0\text{ V}$	$T_{vj} = 25\text{ }^\circ\text{C}$		49	μJ
			$T_{vj} = 175\text{ }^\circ\text{C}$		95	
Turn-off energy	E_{off}	$V_{DD} = 800\text{ V}$, $I_D = 8.9\text{ A}$, $V_{GS} = 0/18\text{ V}$, $R_{GS(on)} = 2.3\ \Omega$, $R_{GS(off)} = 2.3\ \Omega$, $L_\sigma = 15\text{ nH}$, diode: body diode at $V_{GS} = 0\text{ V}$	$T_{vj} = 25\text{ }^\circ\text{C}$		16	μJ
			$T_{vj} = 175\text{ }^\circ\text{C}$		19.7	

(table continues...)

Table 4 (continued) **Characteristic values**

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Total switching energy ¹⁾	E_{tot}	$V_{DD} = 800\text{ V}, I_D = 8.9\text{ A},$ $V_{GS} = 0/18\text{ V},$ $R_{GS(on)} = 2.3\ \Omega,$ $R_{GS(off)} = 2.3\ \Omega,$ $L_\sigma = 15\text{ nH},$ diode: body diode at $V_{GS} = 0\text{ V}$	$T_{vj} = 25\text{ }^\circ\text{C}$		96	μJ
			$T_{vj} = 175\text{ }^\circ\text{C}$		201.7	
Virtual junction temperature	T_{vj}		-55		175	$^\circ\text{C}$
Virtual junction temperature	$T_{vj(over)}$	overload, cumulative max. 100 h ²⁾			200	$^\circ\text{C}$

1) including E_{fr}

2) up to 5000 cycles. Maximum ΔT limited to 100 K.

Note: The chip technology was characterized up to 200 kV/ μs . The measured dV/dt was limited by measurement test setup and package.

Characteristics at $T_{vj} = 25^\circ\text{C}$, unless otherwise specified.

3 Body diode (MOSFET)

Table 5 **Maximum rated values**

Parameter	Symbol	Note or test condition	Values	Unit
Drain-source voltage	V_{DSS}	$T_{vj} \geq 25\text{ }^\circ\text{C}$	1200	V
Peak reverse drain current, t_p limited by $T_{vj(max)}$	I_{SM}	$V_{GS} = 0\text{ V}$	23	A

Table 6 **Characteristic values**

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Drain-source reverse voltage	V_{SD}	$I_{SD} = 8.9\text{ A}, V_{GS} = 0\text{ V}$	$T_{vj} = 25\text{ }^\circ\text{C}$		4.2	V
			$T_{vj} = 100\text{ }^\circ\text{C}$		4.11	
			$T_{vj} = 175\text{ }^\circ\text{C}$		4.05	
MOSFET forward recovery charge	Q_{fr}	$V_{DD} = 800\text{ V},$ $I_{SD} = 8.9\text{ A}, V_{GS} = 0\text{ V},$ $-di_{SD}/dt = 1000\text{ A}/\mu\text{s}, Q_{fr}$ includes also Q_C	$T_{vj} = 25\text{ }^\circ\text{C}$		0.13	μC
			$T_{vj} = 175\text{ }^\circ\text{C}$		0.21	
MOSFET peak forward recovery current	I_{frm}	$V_{DD} = 800\text{ V},$ $I_{SD} = 8.9\text{ A}, V_{GS} = 0\text{ V},$ $-di_{SD}/dt = 1000\text{ A}/\mu\text{s}, Q_{fr}$ includes also Q_C	$T_{vj} = 25\text{ }^\circ\text{C}$		4.5	A
			$T_{vj} = 175\text{ }^\circ\text{C}$		6.1	

(table continues...)

3 Body diode (MOSFET)

Table 6 (continued) Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
MOSFET forward recovery energy	E_{fr}	$V_{DD} = 800\text{ V}$, $I_{SD} = 8.9\text{ A}$, $V_{GS} = 0\text{ V}$, $-di_{SD}/dt = 1000\text{ A}/\mu\text{s}$, Q_{fr} includes also Q_C	$T_{vj} = 25\text{ °C}$		31	μJ
			$T_{vj} = 175\text{ °C}$		87	
Virtual junction temperature	T_{vj}		-55		175	$^{\circ}\text{C}$
Virtual junction temperature	$T_{vj(over)}$	overload, cumulative max. 100 h ¹⁾			200	$^{\circ}\text{C}$

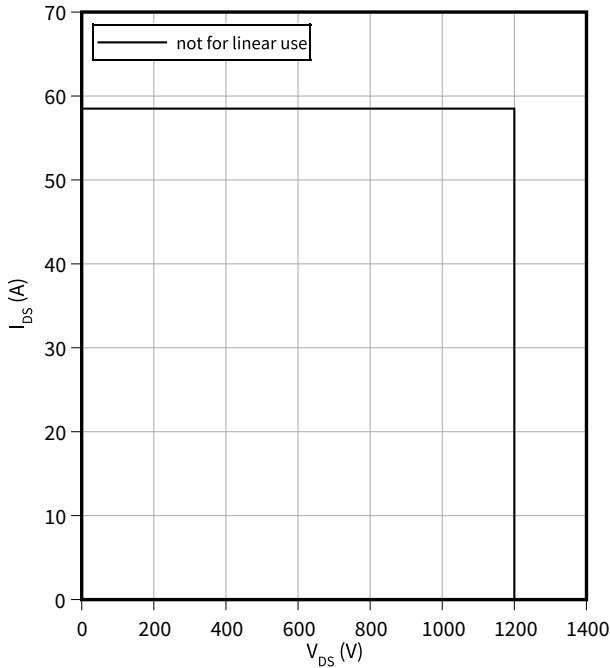
1) up to 5000 cycles. Maximum ΔT limited to 100 K.

4 Characteristics diagrams

Reverse bias safe operating area (RBSOA)

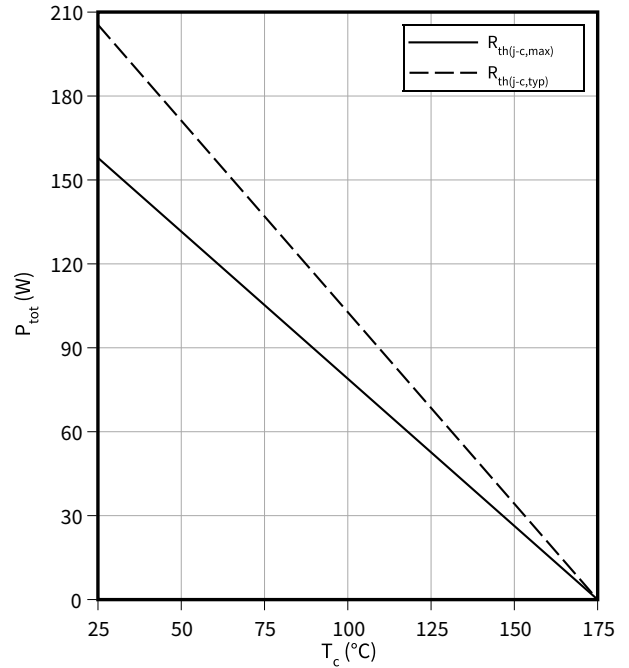
$$I_{DS} = f(V_{DS})$$

$$V_{GS} = 0/18 \text{ V}, T_c = 25 \text{ }^\circ\text{C}, T_{vj} \leq 200 \text{ }^\circ\text{C}$$



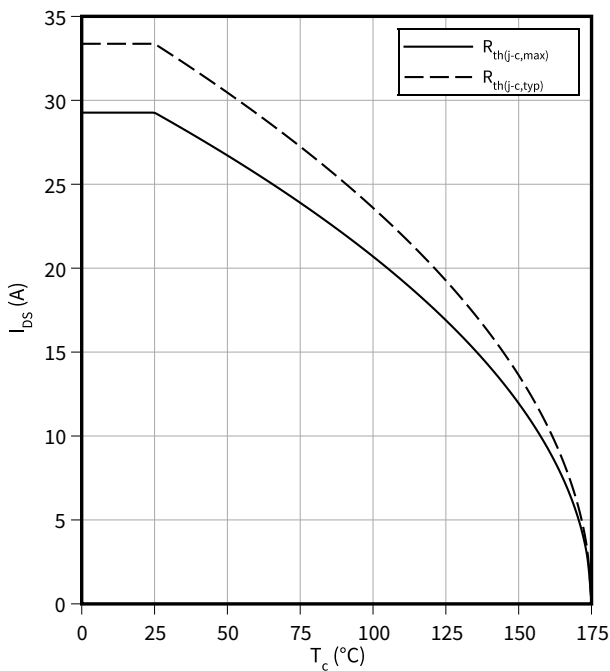
Power dissipation as a function of case temperature

$$P_{tot} = f(T_c)$$



Maximum DC drain to source current as a function of case temperature limited by bond wire

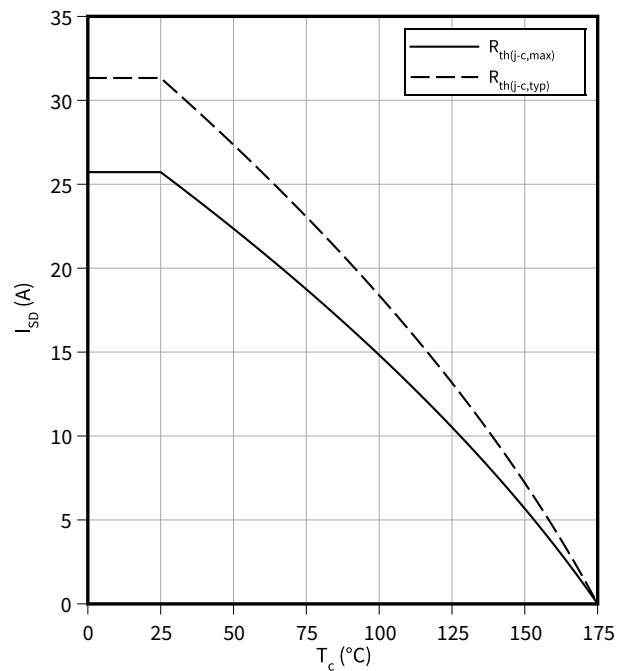
$$I_{DS} = f(T_c)$$



Maximum source to drain current as a function of case temperature limited by bond wire

$$I_{SD} = f(T_c)$$

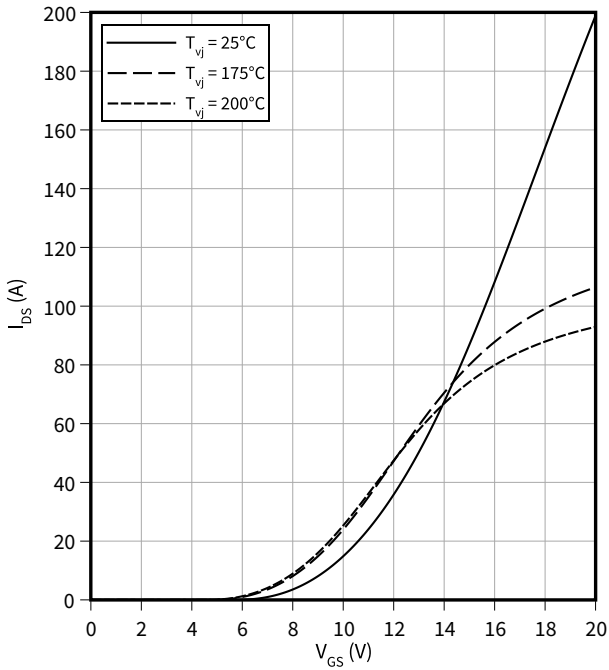
$$V_{GS} = 0 \text{ V}$$



4 Characteristics diagrams

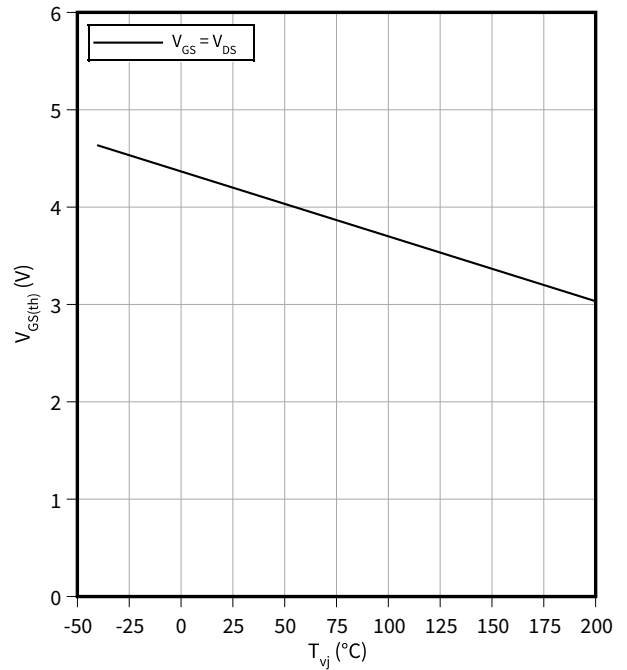
Typical transfer characteristic

$I_{DS} = f(V_{GS})$
 $V_{DS} = 20 \text{ V}$, $t_p = 20 \mu\text{s}$



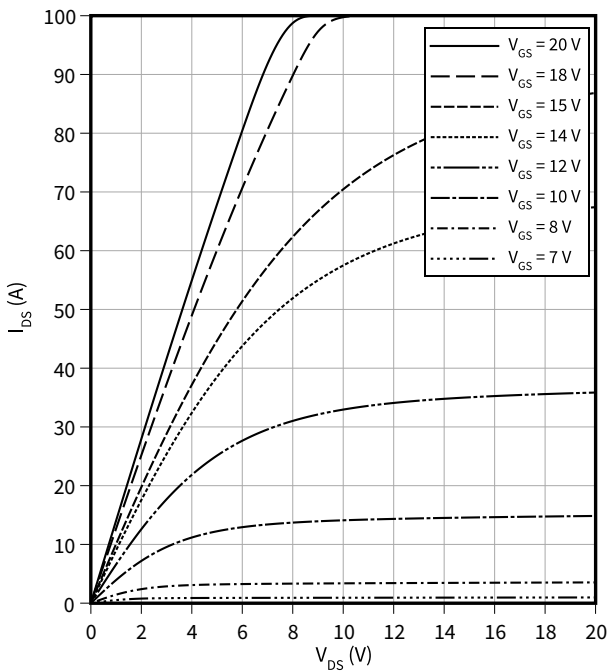
Typical gate-source threshold voltage as a function of junction temperature

$V_{GS(th)} = f(T_{vj})$
 $I_D = 2.8 \text{ mA}$



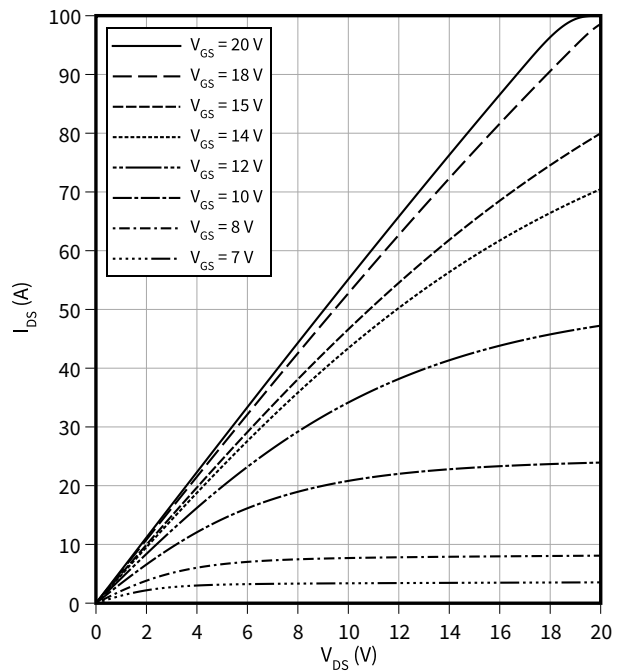
Typical output characteristic, V_{GS} as parameter

$I_{DS} = f(V_{DS})$
 $T_{vj} = 25 \text{ °C}$, $t_p = 20 \mu\text{s}$



Typical output characteristic, V_{GS} as parameter

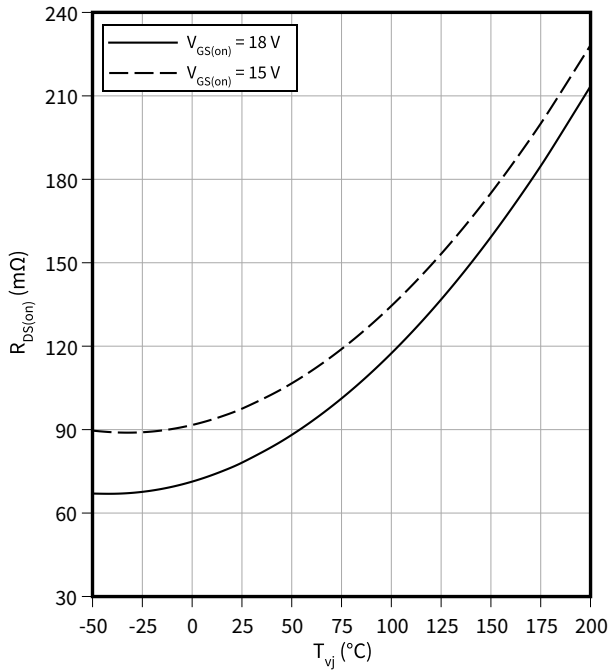
$I_{DS} = f(V_{DS})$
 $T_{vj} = 175 \text{ °C}$, $t_p = 20 \mu\text{s}$



4 Characteristics diagrams

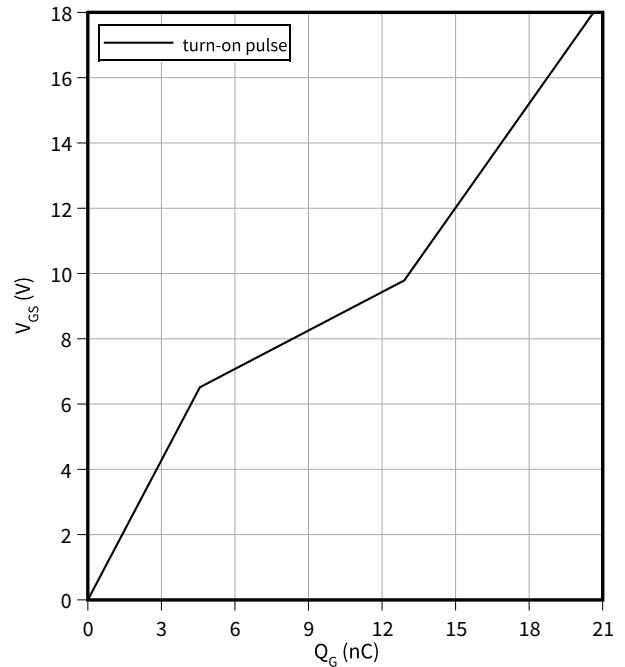
Typical on-state resistance as a function of junction temperature

$R_{DS(on)} = f(T_{vj})$
 $I_D = 8.9 \text{ A}$



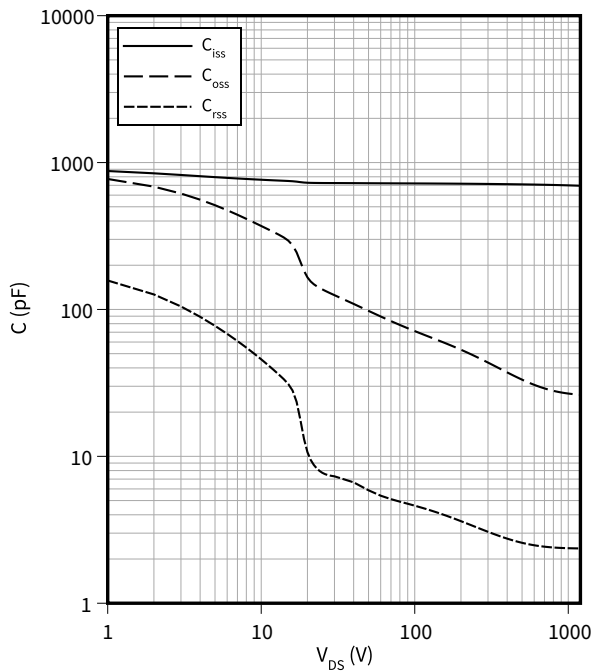
Typical gate charge

$V_{GS} = f(Q_G)$
 $I_D = 8.9 \text{ A}, V_{DS} = 800 \text{ V}$



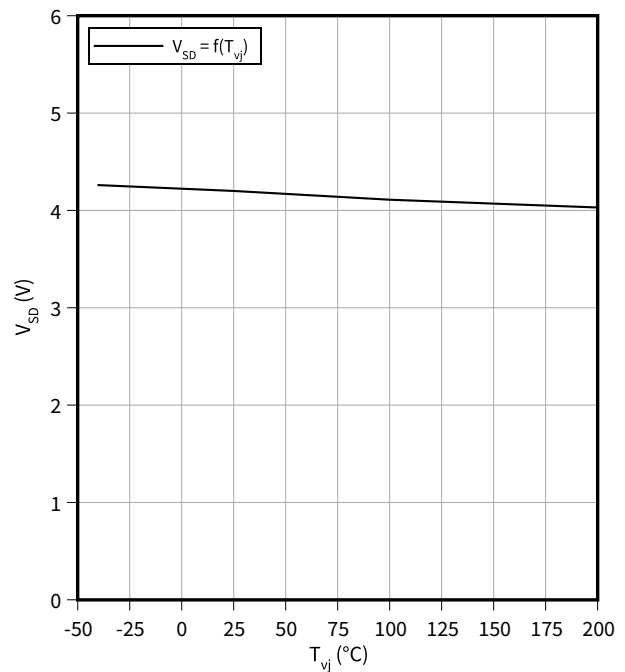
Typical capacitance as a function of drain-source voltage

$C = f(V_{DS})$
 $f = 100 \text{ kHz}, V_{GS} = 0 \text{ V}$



Typical reverse drain voltage as function of junction temperature

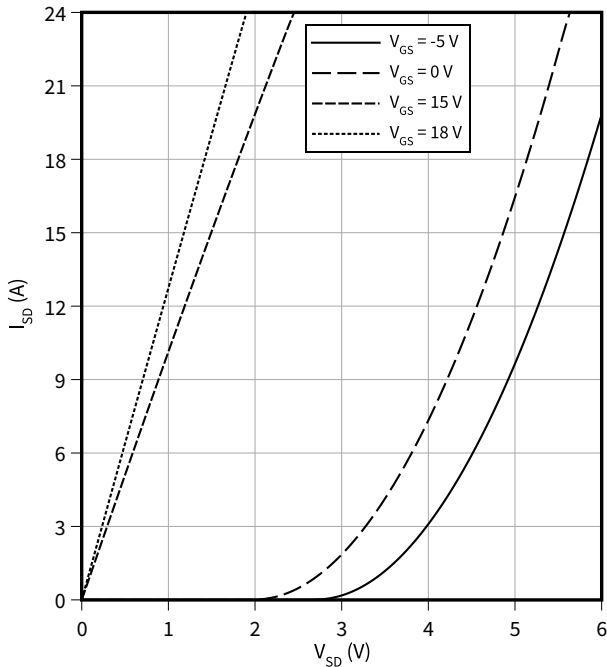
$V_{SD} = f(T_{vj})$
 $I_{SD} = 8.9 \text{ A}, V_{GS} = 0 \text{ V}$



4 Characteristics diagrams

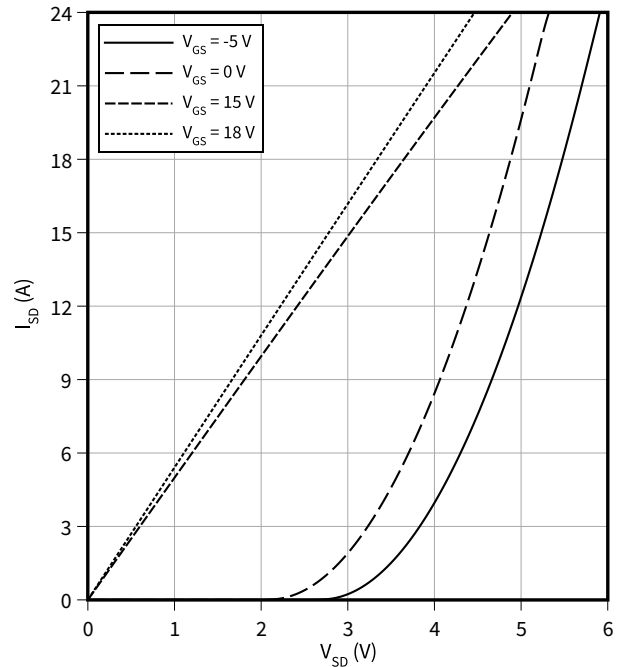
Typical reverse drain current as function of reverse drain voltage, V_{GS} as parameter

$I_{SD} = f(V_{SD})$
 $T_{vj} = 25\text{ °C}$, $t_p = 20\text{ }\mu\text{s}$



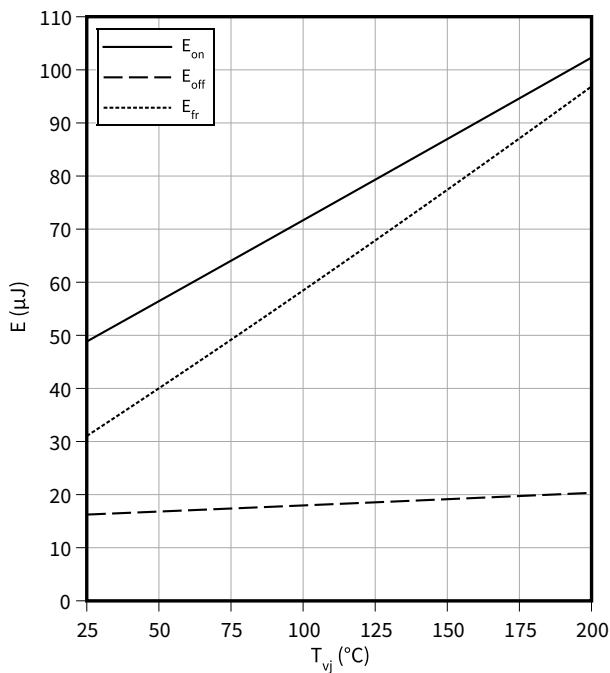
Typical reverse drain current as function of reverse drain voltage, V_{GS} as parameter

$I_{SD} = f(V_{SD})$
 $T_{vj} = 175\text{ °C}$, $t_p = 20\text{ }\mu\text{s}$



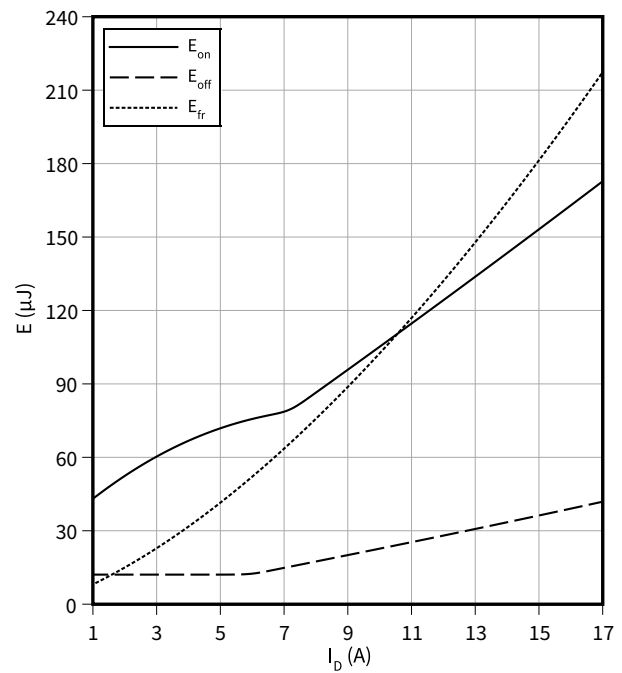
Typical switching energy as a function of junction temperature, test circuit in Fig. F, 2nd device own body diode: $V_{GS} = 0\text{ V}$

$E = f(T_{vj})$
 $V_{GS} = 0/18\text{ V}$, $I_D = 8.9\text{ A}$, $R_{G,ext} = 2.3\text{ }\Omega$, $V_{DD} = 800\text{ V}$



Typical switching energy as a function of drain current, test circuit in Fig. F, 2nd device own body diode: $V_{GS} = 0\text{ V}$

$E = f(I_D)$
 $V_{GS} = 0/18\text{ V}$, $T_{vj} = 175\text{ °C}$, $R_{G,ext} = 2.3\text{ }\Omega$, $V_{DD} = 800\text{ V}$

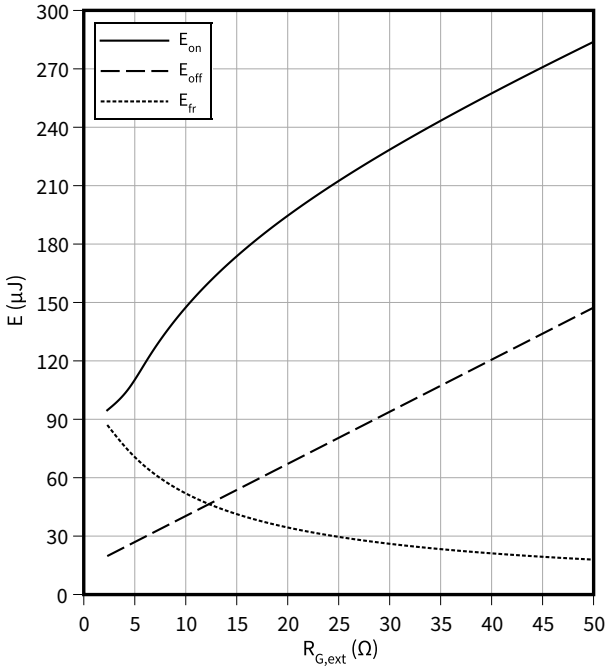


4 Characteristics diagrams

Typical switching energy as a function of gate resistance, test circuit in Fig. F, 2nd device own body diode: $V_{GS} = 0\text{ V}$

$E = f(R_{G,ext})$

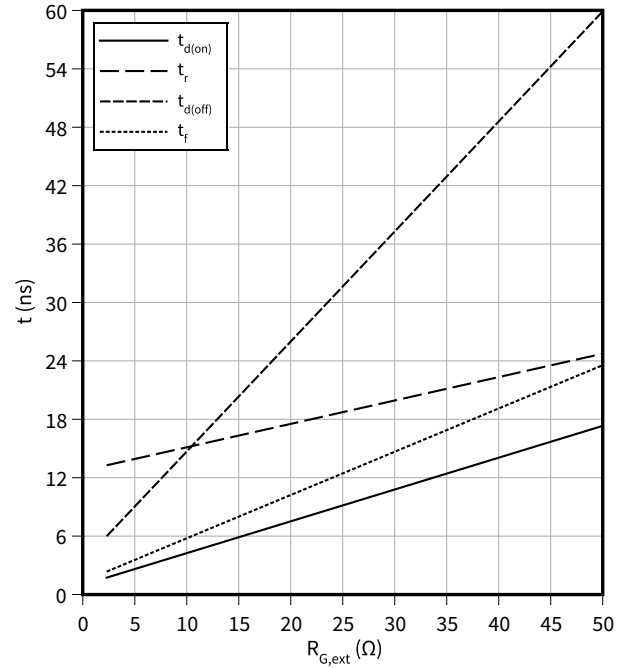
$V_{GS} = 0/18\text{ V}$, $I_D = 8.9\text{ A}$, $T_{vj} = 175\text{ °C}$, $V_{DD} = 800\text{ V}$



Typical switching times as a function of gate resistance, test circuit in Fig. F, 2nd device own body diode: $V_{GS} = 0\text{ V}$

$t = f(R_{G,ext})$

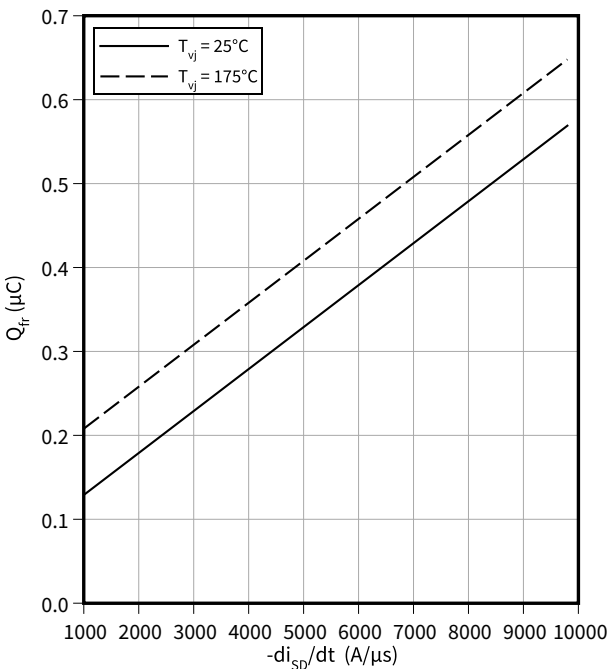
$V_{GS} = 0/18\text{ V}$, $I_D = 8.9\text{ A}$, $T_{vj} = 175\text{ °C}$, $V_{DD} = 800\text{ V}$



Typical reverse recovery charge as a function of reverse drain current slope, test circuit in Fig. F, 2nd device own body diode: $V_{GS} = 0\text{ V}$

$Q_{fr} = f(-di_{SD}/dt)$

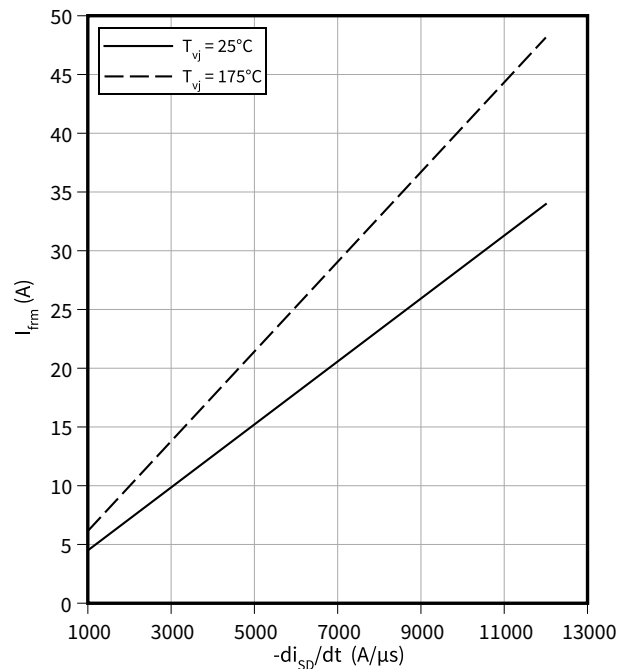
$V_{GS} = 0/18\text{ V}$, $I_{SD} = 8.9\text{ A}$, $V_{DD} = 800\text{ V}$



Typical reverse recovery current as a function of reverse drain current slope, test circuit in Fig. F, 2nd device own body diode: $V_{GS} = 0\text{ V}$

$I_{frm} = f(-di_{SD}/dt)$

$V_{GS} = 0/18\text{ V}$, $I_{SD} = 8.9\text{ A}$, $V_{DD} = 800\text{ V}$



4 Characteristics diagrams

Typical switching energy as a function of dead time / blanking time, test circuit in Fig. F, 2nd device own body diode: $V_{GS} = -5\text{ V}$

$$E = f(t_{\text{dead}})$$

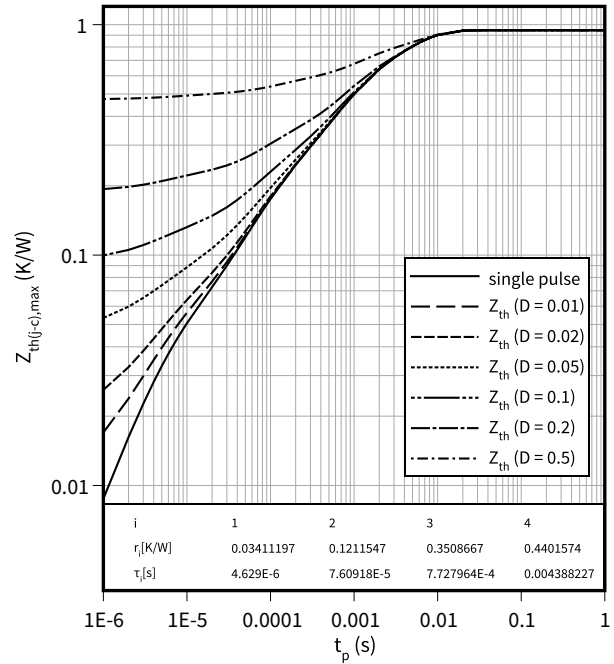
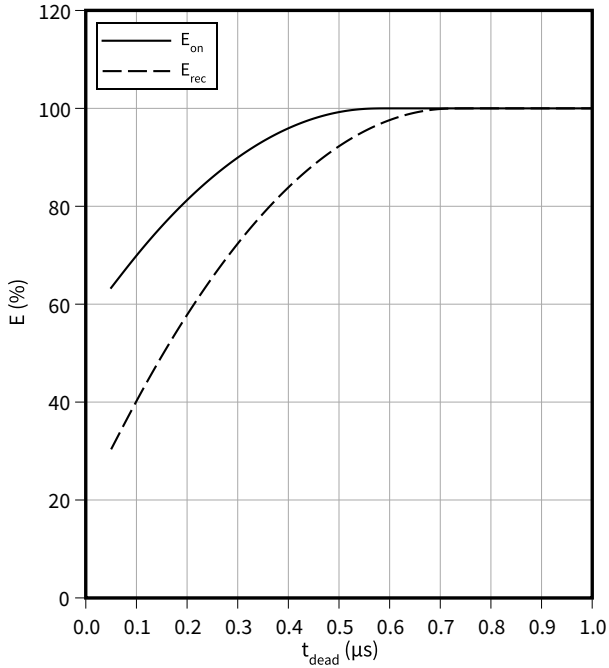
$V_{GS} = 0/18\text{ V}$, $I_D = 8.9\text{ A}$, $T_{vj} = 175\text{ °C}$, $R_{G,\text{ext}} = 2.3\ \Omega$

$V_{DD} = 800\text{ V}$

Max. transient thermal impedance (MOSFET/diode)

$$Z_{\text{th}(j-c),\text{max}} = f(t_p)$$

$$D = t_p/T$$



5 Package outlines

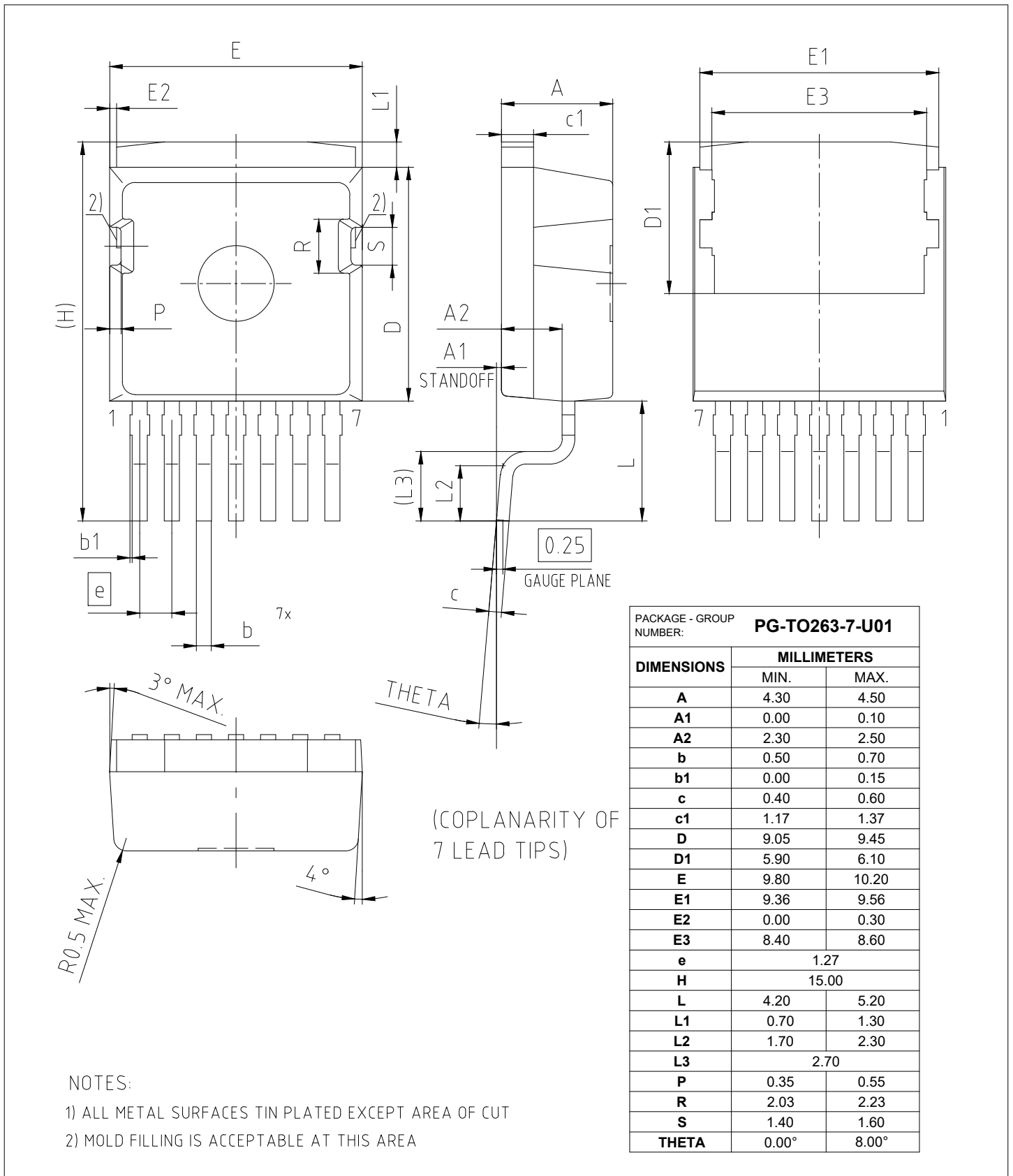


Figure 1

6 Testing conditions

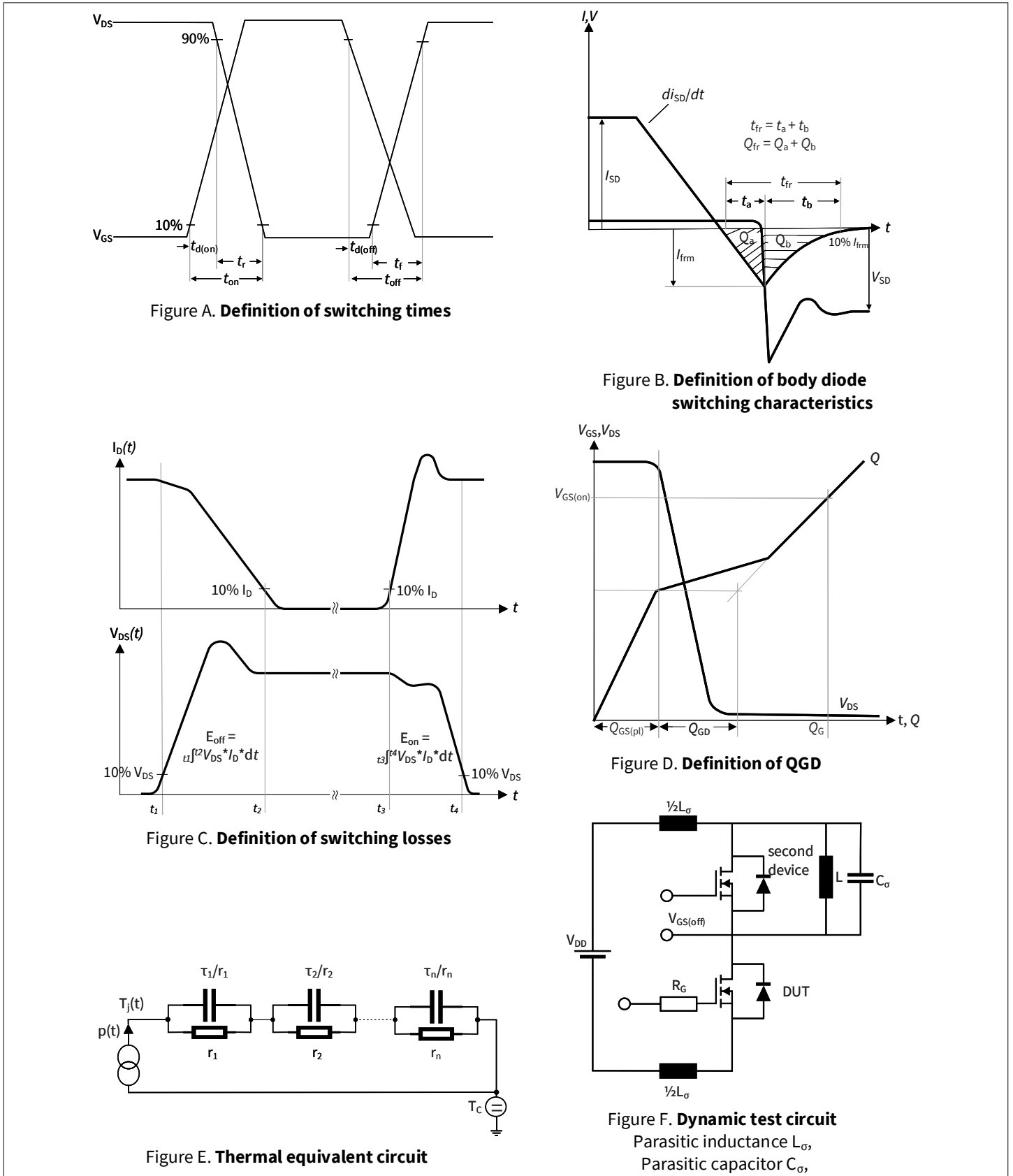


Figure 2

Revision history

Document revision	Date of release	Description of changes
0.10	2023-08-09	Preliminary datasheet
1.00	2023-10-05	Final datasheet
1.10	2024-01-12	Negative gate voltage values updated Resistance parameters updated Additional capacitance & charge values added E = f(t _{dead}) graph y-axis correction to percentage values Editorial changes
1.20	2024-07-02	Updated „Potential applications“ Corrected package name Corrected static and dynamic gate-source voltage Corrected unit of L to μH for “Avalanche energy, repetitive” Corrected value of g _{fs} in the Table 4 Corrected diagrams "Typical transfer characteristic" and "Max. transient thermal impedance (MOSFET/diode)" Updated Figure D. Definition of QGD
1.30	2024-11-08	Corrected diagram I _{frm} = f(-di _{SD} /dt) Editorial changes

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